N-channel 40 V, 15.0 mΩ logic level MOSFET in LFPAK33
10 January 2025 Product data sheet

1. General description

Automotive qualified logic level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
 - · Low power losses, high power density
- · LFPAK copper clip package technology:
 - · High robustness and reliability
 - · Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

3. Applications

- 12 V automotive systems
- · Powertrain, chassis, body and infotainment applications
- · Medium/Low power motor drive
- · DC-DC systems
- · LED lighting

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|------|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | - | 30 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 44 | W |
| Static characte | ristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11 | | 8.4 | 12.1 | 15 | mΩ |
| Dynamic chara | cteristics | | | | | | |
| Q_{GD} | gate-drain charge | I _D = 10 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 13; Fig. 14 | | - | 1.2 | 2.5 | nC |
| Source-drain d | iode | | | | | | |
| Q _r | recovered charge | $I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$ | | - | 11 | - | nC |



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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------|-----------------|---|-----|------|-----|------|
| S | softness factor | I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C | - | 0.57 | - | |

^{[1] 30}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|--|
| 1 | S | source | | |
| 2 | S | source | | D |
| 3 | S | source | | |
| 4 | G | gate | | G_(↓□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□□ |
| mb | D | Mounting base; connected to drain | 1 2 3 4 | mbb076 S |
| | | | LFPAK33 (SOT1210) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| BUK9M15-40H | | Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch | SOT1210 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9M15-40H | 91540H |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | 40 | V |
| V_{GS} | gate-source voltage | | [1] | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | 44 | W |
| I_D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [2] | - | 30 | А |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | | - | 27.4 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3 | | - | 155 | А |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|---------|-----|------|------|
| Source-drain | n diode | | | • | | |
| Is | source current | T _{mb} = 25 °C | | - | 30 | Α |
| I _{SM} | peak source current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C | | - | 155 | Α |
| Avalanche ru | uggedness | | | ' | ' | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | I_D = 30 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [3] [4] | - | 10.7 | mJ |

- [1] Refer to application note AN90001 for further information.
- [2] 30A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

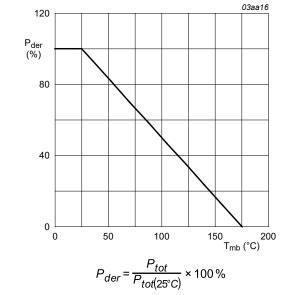
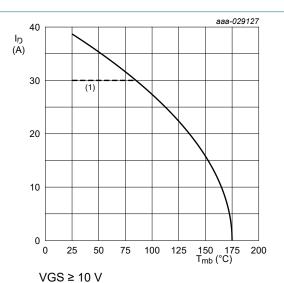


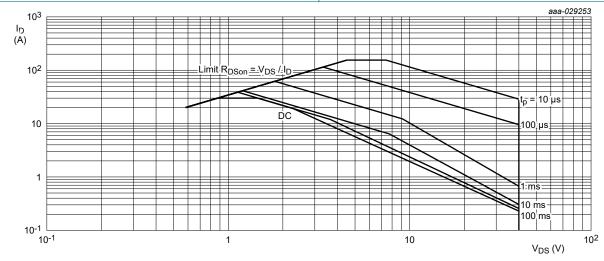
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 30A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design

Fig. 2. Continuous drain current as a function of mounting base temperature

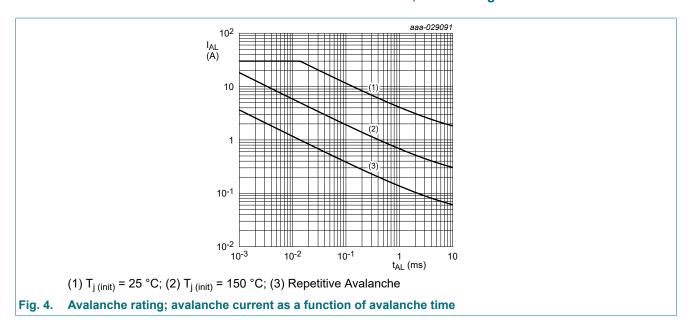
and operating temperature.



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

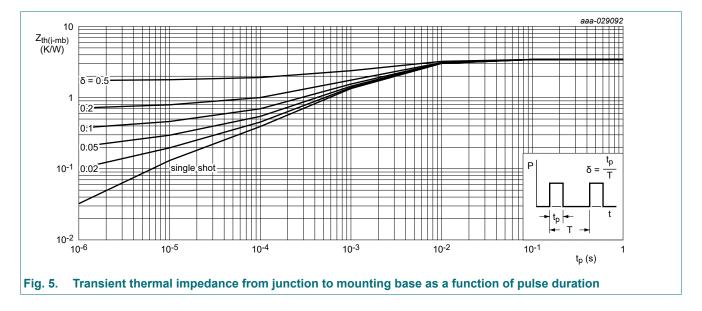
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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------|---|---------------|-----|------|------|------|
| | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | 3.22 | 3.44 | K/W |



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10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|---|------|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source | I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C | 40 | 43 | - | V |
| , | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C | - | 40.5 | - | V |
| | | I _D = 250 µA; V _{GS} = 0 V; T _i = -55 °C | 36 | 40 | _ | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u> ; <u>Fig. 10</u> | 1.5 | 1.85 | 2.2 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$ | - | - | 2.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10 | 0.7 | - | - | V |
| DSS | drain leakage current | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.01 | 5 | μA |
| | | V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C | - | 0.24 | 10 | μA |
| | | V _{DS} = 40 V; V _{GS} = 0 V; T _i = 175 °C | - | 17 | 500 | μΑ |
| l _{GSS} | gate leakage current | V _{GS} = 16 V; V _{DS} = 0 V; T _i = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11 | 8.4 | 12.1 | 15 | mΩ |
| | | V _{GS} = 10 V; I _D = 10 A; T _j = 105 °C; Fig. 12 | 11.5 | 17.3 | 22.5 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 12 | 12.6 | 18.8 | 24.2 | mΩ |
| | | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 °C;$ Fig. 12 | 15.3 | 22.7 | 29.1 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11 | 10.6 | 15.3 | 19 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 105 ^{\circ}\text{C};$ Fig. 12 | 14.5 | 21.7 | 28.5 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 125 ^{\circ}\text{C};$ Fig. 12 | 16 | 23.4 | 30.6 | mΩ |
| | | V_{GS} = 4.5 V; I_{D} = 10 A; T_{j} = 175 °C; Fig. 12 | 19.4 | 28.1 | 36.9 | mΩ |
| R_G | gate resistance | f = 1 MHz; T _j = 25 °C | 0.3 | 0.9 | 2.3 | Ω |
| Dynamic ch | naracteristics | | | | | |
| $Q_{G(tot)}$ | total gate charge | I _D = 10 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 13; Fig. 14 | - | 11.6 | 16.2 | nC |
| | | I _D = 10 A; V _{DS} = 20 V; V _{GS} = 4.5 V; | - | 5.3 | 7.4 | nC |
| Q_{GS} | gate-source charge | Fig. 13; Fig. 14 | - | 2.2 | 3.3 | nC |
| Q_{GD} | gate-drain charge | | - | 1.2 | 2.5 | nC |
| Siss | input capacitance | V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; | - | 733 | 1026 | pF |
| Coss | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | - | 247 | 346 | pF |
| C _{rss} | reverse transfer capacitance | | - | 28 | 62 | pF |
| d(on) | turn-on delay time | $V_{DS} = 20 \text{ V}; R_L = 2 \Omega; V_{GS} = 4.5 \text{ V};$ | - | 7.3 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | - | 5.9 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 8.1 | - | ns |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------|-----------------------|---|--|-----|------|-----|------|
| t _f | fall time | | | - | 4.1 | - | ns |
| Source-dra | in diode | | | | ' | ' | ' |
| V_{SD} | source-drain voltage | I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u> | | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ | | - | 19 | - | ns |
| Q _r | recovered charge | V _{DS} = 20 V | | - | 11 | - | nC |
| S | softness factor | I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C | | - | 0.57 | - | |
| | | I_S = 10 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C | | - | 0.36 | - | |

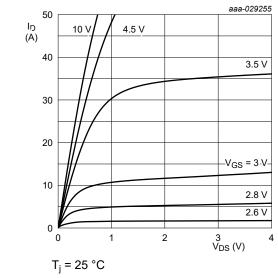


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

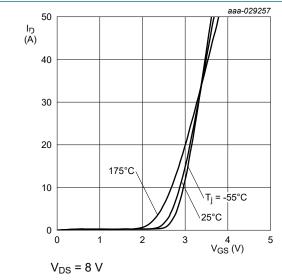


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

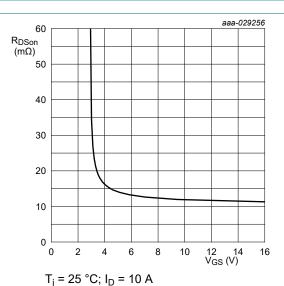
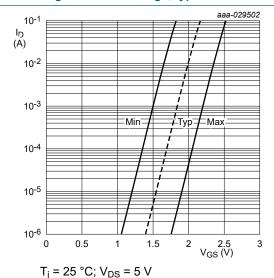


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



1) 20 0, 105 0 1

Fig. 9. Sub-threshold drain current as a function of gate-source voltage

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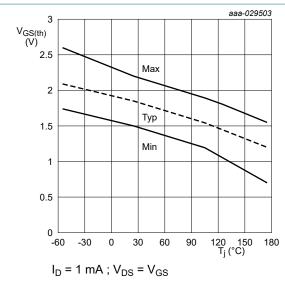


Fig. 10. Gate-source threshold voltage as a function of junction temperature

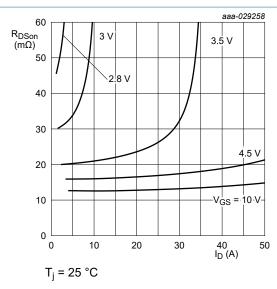


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

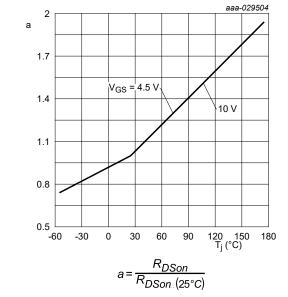


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

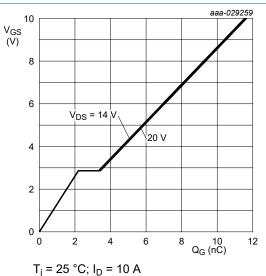


Fig. 13. Gate-source voltage as a function of gate charge; typical values

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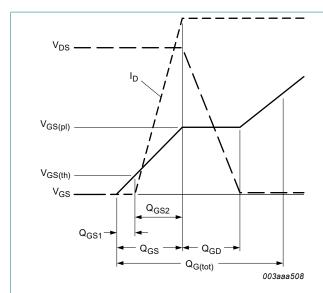
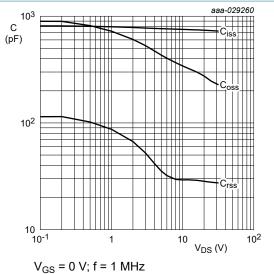


Fig. 14. Gate charge waveform definitions



VGS 0 V, 1 1 1 1 1 1 2

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

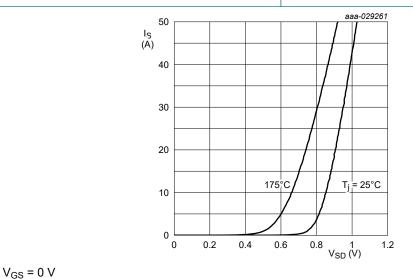


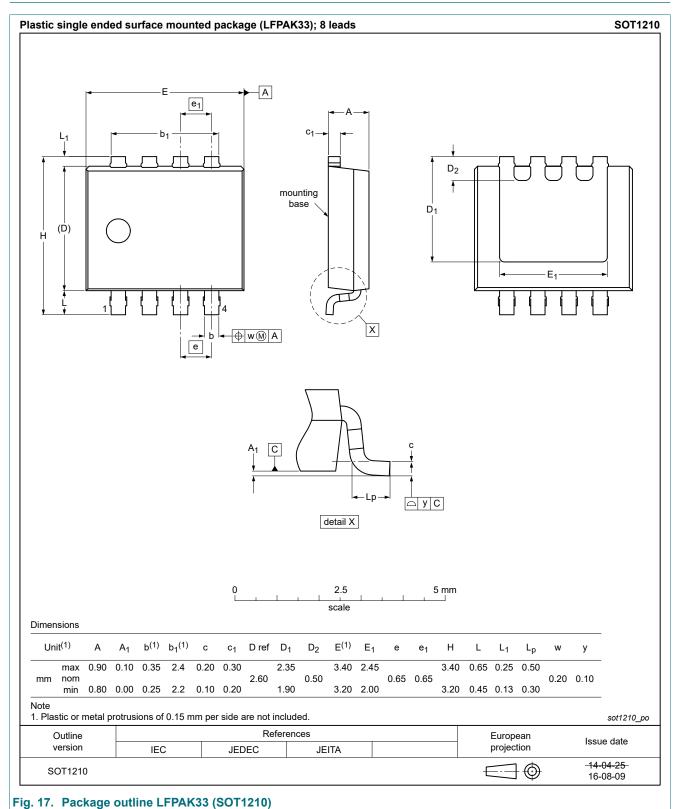
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

Product data sheet

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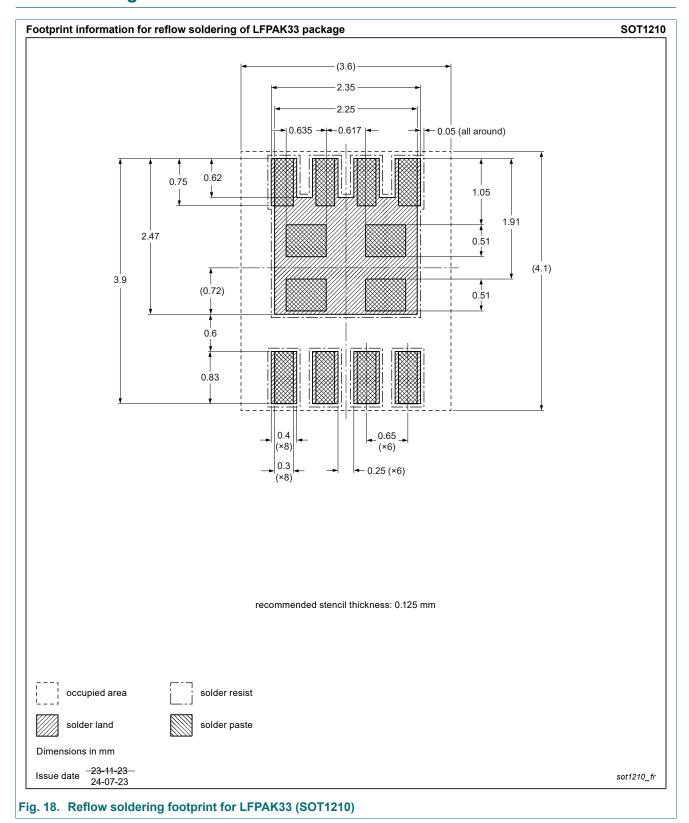
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11. Package outline



N-channel 40 V, 15.0 m Ω logic level MOSFET in LFPAK33

12. Soldering



BUK9M15-40H

N-channel 40 V, 15.0 mΩ logic level MOSFET in LFPAK33

13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
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